

Including radiation damage effects in ATLAS Monte Carlo simulation: Status and perspectives

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In hybrid pixel modules:

- Radiation effects on readout chips
 - Single event upsets in digital parts of readout chip
 - TID effects on transistor leakage current
- Radiation effects on sensor bulk
 - Change of effective doping concentration \rightarrow type inversion and change of depletion voltage
 - Loss of charge collection efficiency
 - Shift of Lorentz angle
 - In order to compensate: modify bias voltage and retuning
 - Disclaimer: we will not talk about effects on the readout chip





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- Radiation effective readout
 - Single even and parts of readout chip
 - TID effection transistor less age current
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→ c.f. talk on Friday: Operational Experience and Performance with the ATLAS Pixel Detector at the Large Hadron Collider

The ATLAS Pixel Detector



- Four layer pixelated detector with three end–caps on each side
- Inner layer (IBL) was inserted later at about 3 cm distance from interaction point
 - IBL uses planar 200 μm thick sensors with 250 μm x 50 μm pixel pitch
 - Most modules are planar n⁺-in-n
 - Forward modules are n⁺-in-p 3D sensors (230 μm thick)
 - The innermost layer of the ATLAS Inner Tracker upgrade will use 3D sensors
 - Other Pixel layers and disks
 - Innermost is the B-Layer at r = 5 cm
 - 250 μm thick n⁺-in n-sensors
 - 400 μm x 50 μm pixels





FBK: pass-through

columns, p-spray isolation



Bump

isolated with p-stop implants

Radiation: present and future



- About 290 fb⁻¹ of collisions delivered to ATLAS so far
- To IBL about 30 fb⁻¹ less due to later installation
- We aim at 160 fb^{-1} more for the rest of the project
- Innermost layers in the ATLAS Inner Tracker upgrade are targeted to withstand 2000 fb⁻¹ of radiation
- Conversion from integrated luminosity to fluence?

	IBL		B-Layer	
	Fluence [1 MeV n _{eq} /cm ²]	Int. Lumi [fb ⁻¹]	Fluence [1 MeV n _{eq} /cm ²]	Int. Lumi [fb ⁻¹]
Current	~1.2 x 10 ¹⁵	260	~0.9 x 10 ¹⁵	290
Design	5 x 10 ¹⁵		1 x 10 ¹⁵	
EOL projection	2.1 x 10 ¹⁵	395	1.5 x 10 ¹⁵	425
80 ATLAS Online Luminosity (pp Only!) 70 2011 pp (\$s = 7 TeV (pp Only!) 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2017 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2017 pp (\$s = 13 TeV 2015 pp (\$s = 13 TeV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV 2017 pp (\$s = 13 teV 2015 pp (\$s = 13 teV				

Month in Year

From luminosity to fluence



Data (Hamburg + Leakage Current)

Sim. (Pythia 8 A3 + Geant4)

Sim. (Pythia 8 A3 + FLUKA)



- Measurement of luminosity and • extrapolation to fluence
 - Needs simulation of collisions (Pythia) and then transport code through the detector (FLUKA or Geant4)
 - Gives conversion from int. . luminosity to fluence
 - Indirect measurement of fluence . by measurement of leakage current
 - Leakage current is proportional to fluence and voltage
 - Modelling of leakage current . with Hamburg model

→ c.f. ATLAS Collaboration, 2021 JINST 16 P08025



60

Mean SF

80

z [cm]

Modelling radiation damage





- Deposited charged by MIP in the sensor bulk drift to the electrodes due to electric field
 - Field is modified by radiation damage
- Path is deflected by magnetic field of 2 T solenoid + diffusion
 - Lorentz angle
- Charges can be trapped and only induce a fraction of signal
 - Ramo potential
- Digitisation step is used in many ATLAS Monte Carlo physics samples

 \rightarrow c.f. ATLAS Collaboration, 2019 *JINST* **14** P06012



- Electric non-linear fields are simulated in TCAD for different fluences and bias voltages
 - Radiation damage modelled via Chiochia model for planar n-in-n sensors
 - For p-type bulk in 3D sensors, 3-level models (Perugia*, LHCb**)
- *: F. Moscatelli et al., IEEE Trans.
 Nucl. Sci. 63 (2016) 2716
- **: A. Folkestad et al., NIM A874 (2017) 94-102



Input: ramo potential and charge trapping

0.6

0.4

0.2



- Ramo potential solved in TCAD
 - Only signal induced in adjacent pixels is considered (red box)
 - More complex potential for 3D sensors as the two n⁺-columns are electrically connected
- Charged are trapped (drawn from exponential distribution) and their induced charge at final position is computed
 - ns 1/1_e Mean of exponential distribution Electron Trapping Rate $1/(\beta \Phi)$ with Φ the fluence

 - $\beta_{e} = 4.5 \text{ x } 10^{-16} \text{ cm}^{2} \text{ns}^{-1}$ $\beta_{h} = 6.5 \text{ x } 10^{-16} \text{ cm}^{2} \text{ns}^{-1}$









- Cluster charge as measured in end of Run 2/early Run 3 data
- Comparison with radiation damage digitiser (and constant charge digitiser)
- Radiation damage digitiser replaces constant charge digitiser as ATLAS default since Run 3
- Predicted most probable values match to 1%

Charge collection efficiency







- Good prediction of charge collection efficiency for a large range of fluence
- Comparison of planar IBL and 3D IBL (difference fluence due to position) → different radiation models, still good agreement
- Prediction within what we can deal with loss of CCE until end-of-life

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- Charge sharing also well modelled by radiation damage digitiser
- High number of pixels in a cluster in longitudinal direction because of forward position of 3D modules
- Even cumulative distribution of fraction of charge versus number of highest charge-pixels shows very good agreement



Digitiser: now and future



- Novel radiation damage digitiser used in ATLAS Monte Carlo production since Run
 3
- Excellent agreement between data and MC predictions (w.r.t. large deviations with constant charge digitiser)
- For the ATLAS Inner Tracker (ITk) most inner layers: (1 to 2) x 10¹⁶ 1 MeV n_{eq}/cm² after 2000 fb⁻¹
- current digitiser is unfortunately too slow
- \rightarrow need other approach for ITk

- ITk digitiser inspired by CMS template method \rightarrow c.f. 2007 *PoS* Vertex 2007 035
- Lookup tables (LUTs) to determine how much charge induction is where and by how much it is reduced



Template method: allpix²





- Using the allpix² framework, the templates for the ITk digitiser are derived
- allpix² is a full Geant4 based detector simulation which simulates the propagation of charges in sensor bulk + further steps
- A LUT-based propagator based on the ITk digitiser approach has been implemented and is used to compare the "full" simulation vs. LUT approach

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- The new Run 3 radiation damage digiters performs well and is currently used in ATLAS MC production
- The agreement with Run 3 data is impressive
 - Also for the 3D n⁺-in-p pixel sensor
- Despite that, need for faster approach in the future → ITk template approach
- This is currently under development and validation





- HV scans used to monitor depletion voltage with irradiation
- Shown are the data for the IBL 3Ds
- Increase MPV of cluster charge even above full depletion observed due to reduction of charge trapping
- Range between 0.2 to 6 x 10¹⁴
 1 MeV n_{eq}/cm² for given fluences

